

**IN THE SPECIFICATION:**

Please amend the paragraph at page 3, lns. 7-10 as follows:

A high melting point metal film (tungsten) obtained as such includes scarce impurity elements, typically, amount of oxygen included could be reduced to no more than 30 parts per million (ppm), and an electric resistivity of  $20\ \mu\Omega\cdot\text{cm}$  or less, typically  $6\text{-}15\ \mu\Omega\cdot\text{cm}$  could be obtained. The stress of the film was  $-5\times 10^9\text{-}5\times 10^9\text{dyn/cm}^2$ .

Please amend the paragraph at page 30, lns. 9-12 as follows:

The structure of the storage capacitor of the present invention is not necessarily limited to the one shown in embodiment 1. For example, the storage capacitor described in Japanese Patent Application ~~Laid-Open~~ No. Hei 9-316567 (Publication No. Hei 11-133463) or Japanese Patent Application ~~Laid-Open~~ No. Hei 10-254097 (Publication No. 2001-56485) may be used.

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